

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

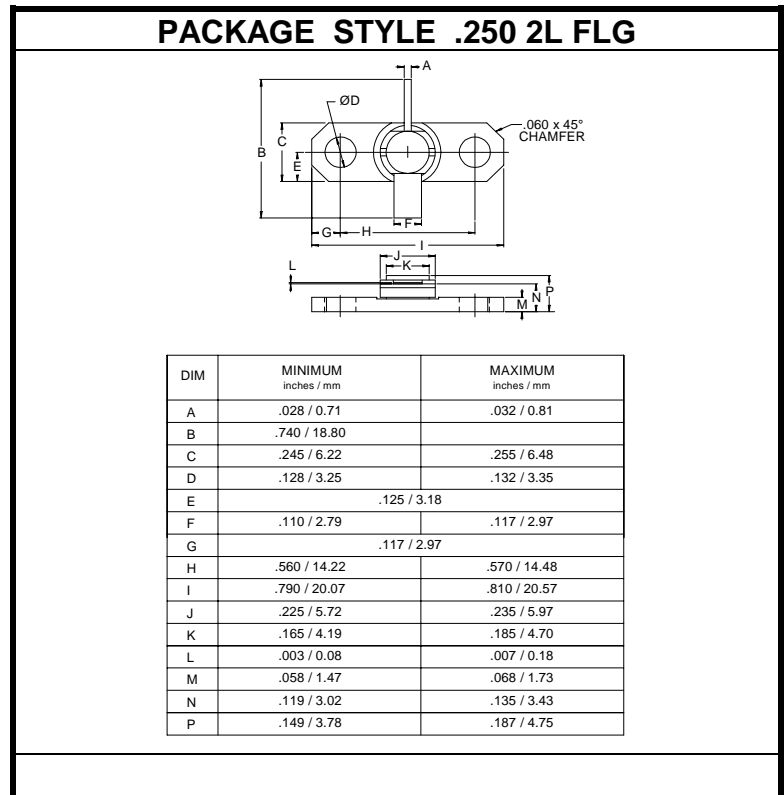
The **ASI MSC81058** is Designed for General Purpose Class C Power Amplifier Applications up to 1.2 GHz.

FEATURES:

- $P_G = 10$ dB min. at 10 W/ 1.0 GHz
- Hermetic Microstrip Package
- **Omnigold™** Metalization System
- Emitter Ballasted

MAXIMUM RATINGS

I_C	1.0 A
V_{CC}	35 V
P_{DISS}	29 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	8.5 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0$ mA	45			V
BV_{CER}	$I_C = 10$ mA $R_{BE} = 10$ Ω	45			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CBO}	$V_{CB} = 28$ V			2.5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	15		120	---
C_{ob}	$V_{CB} = 28$ V $f = 1.0$ MHz			10	pF
P_G	$V_{CC} = 28$ V $P_{OUT} = 10$ W $f = 1.0$ GHz	10	11		dB
η_c		60	64		%